

<SMALL-SIGNAL TRANSISTOR>

# ISC3581AS1

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

ISC3581AS1 is a silicon NPN epitaxial type transistor designed for high collector current application.

Complementary with ISA1399AS1.

## FEATURE

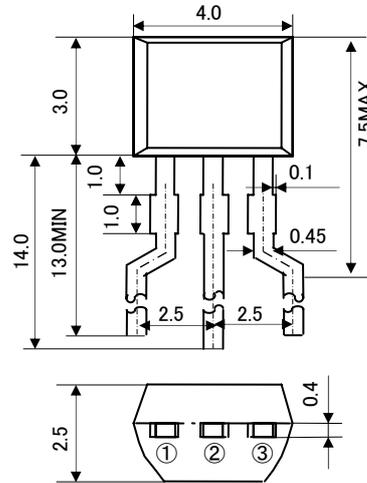
- High collector current.  $I_{CM}=600\text{mA}$
- High gain band width product.  $f_T=150\text{MHz}$  typ
- High  $V_{CEO}$ .  $V_{CEO}=50\text{V}$
- Excellent linearity of DC forward current gain.

## APPLICATION

For switching, small type motor drive application.

## OUTLINE DRAWING

Unit: mm



JEITA: -  
JEDEC: -

### TERMINAL CONNECTER

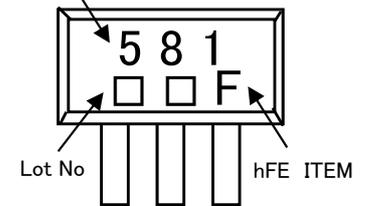
- ①: EMITTER
- ②: COLLECTOR
- ③: BASE

## MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

Symbol	Parameter	Ratings	Unit
$V_{CBO}$	Collector to Base voltage	55	V
$V_{EBO}$	Emitter to Base voltage	4	V
$V_{CEO}$	Collector to Emitter voltage	50	V
$I_C$	Collector current	400	mA
$I_{CM}$	Peak collector current	600	mA
$P_c$	Collector dissipation	600	mW
$T_j$	Junction temperature	+150	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-55~+150	$^\circ\text{C}$

## MARKING

Type name



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C=10\mu\text{A}$ , $I_E=0\text{mA}$	55	-	-	V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=10\mu\text{A}$ , $I_C=0\text{mA}$	4	-	-	V
$V_{(BR)CEO}$	C to E break down voltage	$I_C=100\mu\text{A}$ , $R_{BE}=\infty$	50	-	-	V
$I_{CBO}$	Collector cut off current	$V_{CB}=25\text{V}$ , $I_E=0\text{mA}$	-	-	1	$\mu\text{A}$
$I_{EBO}$	Emitter cut off current	$V_{EB}=2\text{V}$ , $I_C=0\text{mA}$	-	-	1	$\mu\text{A}$
$h_{FE}\text{※}$	DC forward current gain	$V_{CE}=4\text{V}$ , $I_C=100\text{mA}$	90	-	500	-
$V_{CE(sat)}$	C to E Saturation Voltage	$I_C=200\text{mA}$ , $I_B=10\text{mA}$	-	0.15	0.5	V
$f_T$	Gain band width product	$V_{CE}=6\text{V}$ , $I_E=-10\text{mA}$	-	150	-	MHz

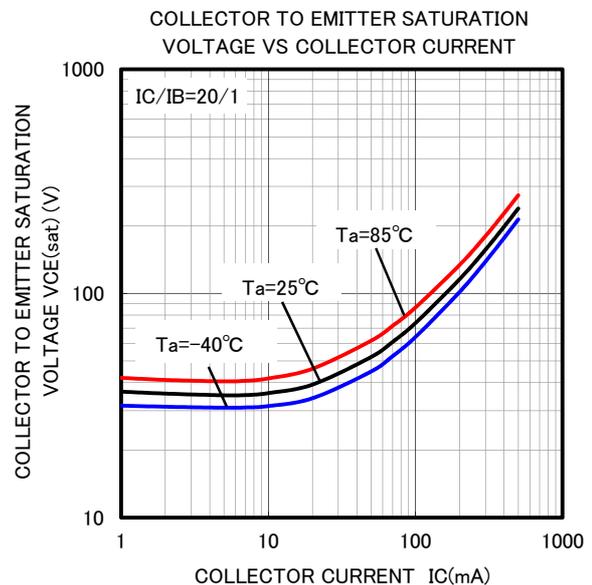
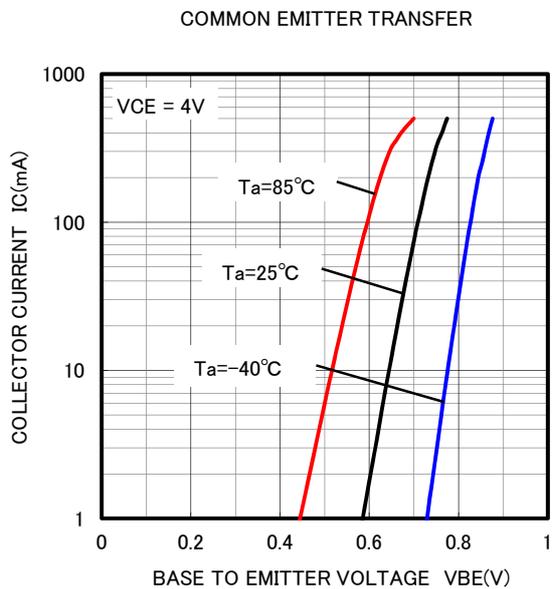
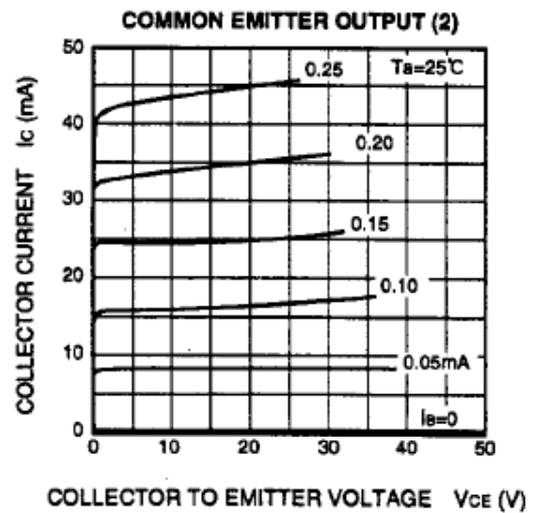
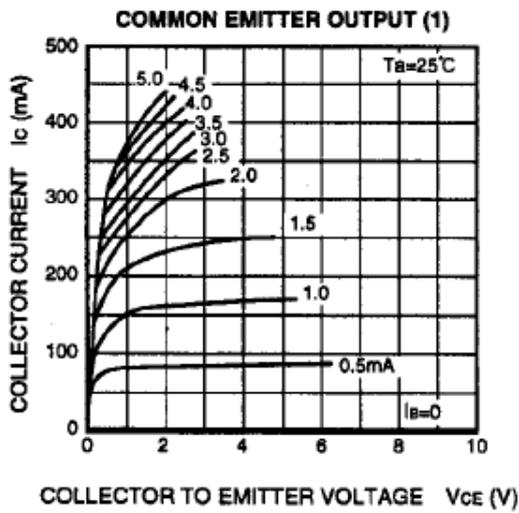
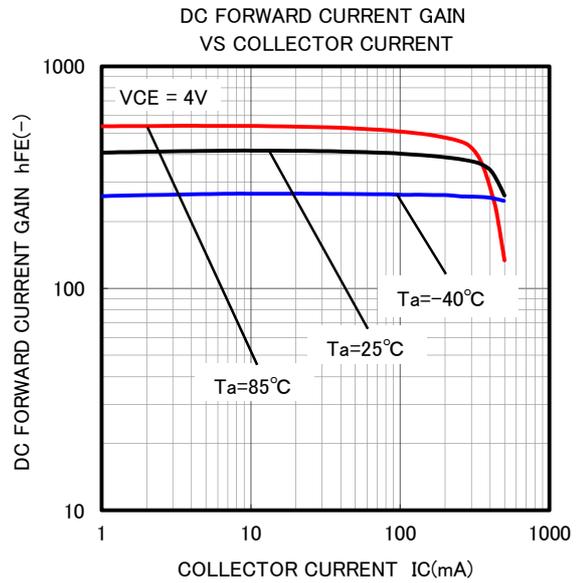
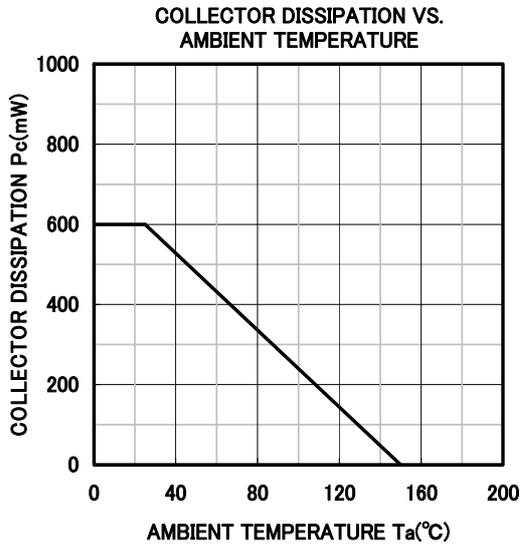
※) It shows  $h_{FE}$  classification in right table.

D	E	F
90~180	150~300	250~500

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## TYPICAL CHARACTERISTICS





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